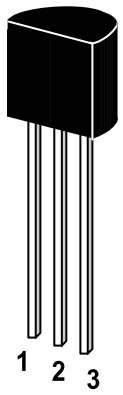
ST 2SC732

NPN Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

The transistor is subdivided into two groups, G and L, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (Ta=25℃)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	5	V
Base Current	I_B	30	mA
Collector Current	I_C	150	mA
Power Dissipation	P_{tot}	400	mW
Junction Temperature	T_j	125	^{O}C
Storage Temperature Range	T_S	-55 to +125	^{O}C

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Characteristics at T_{amb}=25 °C

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V_{CE}=6V, I_C=2mA					
Current Gain Group G	h_{FE}	200	-	400	-
L	h_{FE}	350	-	700	-
Base-Emitter Voltage at V_{CE}=6V,I_C=2mA	V_{BE}	-	0.65	-	V
Collector Cutoff Current at V_{CB}=60V	I_{CBO}	-	-	0.1	μA
Emitter Cutoff Current at V_{EB}=5V	I_{EBO}	-	-	0.1	μA
Collector Saturation Voltage at I_C=10mA, I_B=1mA	$V_{CE(sat)}$	-	-	0.3	V
Gain Bandwidth Product at V_{CE}=6V, I_C=1mA	f_T	-	150	-	MHz
Output Capacitance at V_{CB}=10V, f=1MHz	C_{OB}	-	2	-	pF
Noise Figure at V_{CE}=6V, I_C=0.1mA f=100Hz, R_G=10KΩ	NF(1)	-	0.5	6	V
Noise Figure at V_{CE}=6V, I_C=0.1mA f=1KHz, R_G=10KΩ	NF(2)	-	0.2	3	V